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Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: August 18, 2004

Enter as many sheets as necessary)

Complete if Known

Application Number 10/752,092
 Filing Date 01/07/2004
 First Named Inventor Masatomo SHIBATA
 Group Art Unit 2811-2813
 Examiner Name Unassigned Blum
 Attorney Docket Number 035532-0138

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
B	A1	O. Nam et al., "Lateral epitaxy of low defect density GaN layers via organometallic vapor phase epitaxy", Applied Physics Letters, Vol 71, No. 18, 3 November 1997, pages 2638-2640.	
	A2	M. Kuramoto et al., "Room-Temperature Continuous-Wave Operation of InGaN Multi-Quantum-Well Laser Diodes Grown on an n-GaN Substrate with a Backside n-Contact", Jpn. J. Appl. Phys., Vol. 38, Part 2, No. 2B, 15 Feb. 1999, pages L184-L186.	
	A3	Y. Oshima et al., "Preparation of Freestanding GaN Wafers by Hydride Vapor Phase Epitaxy with Void-Assisted Separation", Jpn. J. Appl. Phys., Vol. 42, Part 2, No. 1A/B, 15 Jan. 2003, pages L1-L3.	
	A4	T. Zheleva et al., "Pendeo-Epitaxy - A New Approach for Lateral Growth of Gallium Nitride Structures", MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999), 6 pages.	
	A5	K. Motoki et al., "Preparation of Large Freestanding GaN Substrates by Hydride Vapor Phase Epitaxy Using GaAs as a Starting Substrate", Jpn. J. Appl. Phys., Vol. 40, Part 2, No. 2B, 15 Feb. 2001, pages L140-L143.	

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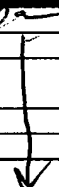
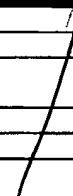
¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: January 7, 2004 (use as many sheets as necessary)				Complete if Known	
Sheet 1 of 1		Application Number <u>Unassigned</u> <u>10/752092</u>		Filing Date <u>01/07/2004</u>	
		First Named Inventor <u>Masatomo SHIBATA</u>		Group Art Unit <u>Unassigned</u> <u>2813</u>	
		Examiner Name <u>Unassigned</u> <u>Blum</u>		Attorney Docket Number <u>035532-0138</u>	

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
	A1	6,413,627	B1	MOTOKI ET AL.	07-02-2002	
	A2	2002/0197825	A1	USUI ET AL.	12-26-2002	
	A3	5,290,393		NAKAMURA	03-01-1994	
	A4	2002/0066403	A1	SUNAKAWA ET AL.	06-06-2002	
	A5	6,555,845	B2	SUNAKAWA ET AL.	04-29-2003	
	A6	6,348,096	B1	SUNAKAWA ET AL.	02-19-2002	
	A7	2003/0080345	A1	MOTOKI ET AL.	05-01-2003	

FOREIGN PATENT DOCUMENTS								
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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
	A8	JP	2003-178984	A	NEC CORP., ET AL.	06-27-2003		Abstract
	A9	JP	11-251253	A	NICHIA CHEM. IND. LTD.	09-17-1999		Abstract
	A10	JP	2000-22212	A	SUMITOMO ELECTRIC IND. LTD.	01-21-2000		Abstract
	A11	JP	4-297023	A	NICHIA CHEM. IND. LTD.	10-21-1992		Abstract
	A12	JP	10-312971	A	NEC CORP.	11-24-1998		Abstract
	A13	JP	2003-165799	A	SUMITOMO ELECTRIC IND. LTD.	06-10-2003		Abstract

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